Memory FeRAM

64 K (8 K \times 8) Bit SPI

MB85RS64T

■ DESCRIPTION

MB85RS64T is a FeRAM (Ferroelectric Random Access Memory) chip in a configuration of 8,192 words \times 8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

MB85RS64T adopts the Serial Peripheral Interface (SPI).

The MB85RS64T is able to retain data without using a back-up battery, as is needed for SRAM. The memory cells used in the MB85RS64T can be used for 10¹³ read/write operations, which is a significant improvement over the number of read and write operations supported by Flash memory and E²PROM. MB85RS64T does not take long time to write data like Flash memories or E²PROM, and MB85RS64T takes no wait time.

■ FEATURES

• Bit configuration : 8,192 words × 8 bits

• Serial Peripheral Interface : SPI (Serial Peripheral Interface)

Correspondent to SPI mode 0 (0, 0) and mode 3 (1, 1)

Operating frequency: 10 MHz (Max)
High endurance : 10¹³ times / byte
Data retention : 10 years (+85 °C)

Operating power supply voltage: 1.8 V to 3.6 V

• Low power consumption : Operating power supply current 0.8 mA (Max@10 MHz)

Standby current 9 µA (Typ)

• Operation ambient temperature range : $-40~^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$

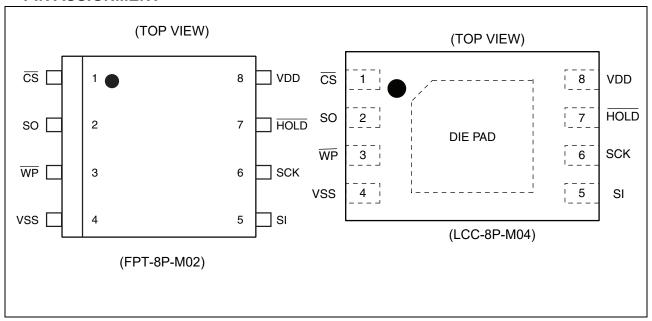
Package : 8-pin plastic SOP (FPT-8P-M02)

8-pin plastic SON (LLC-8P-M04)

RoHS compliant



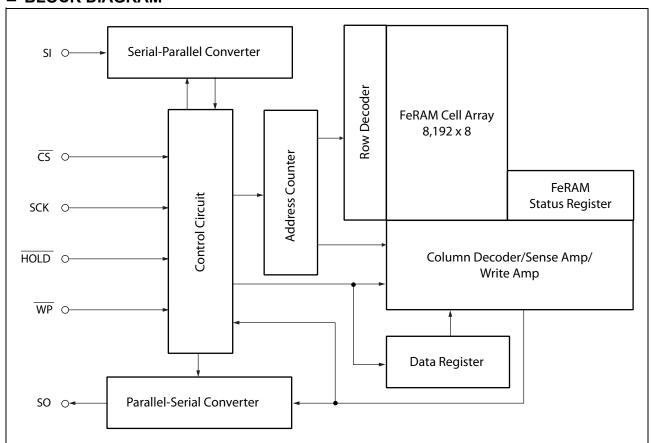
■ PIN ASSIGNMENT



■ PIN FUNCTIONAL DESCRIPTIONS

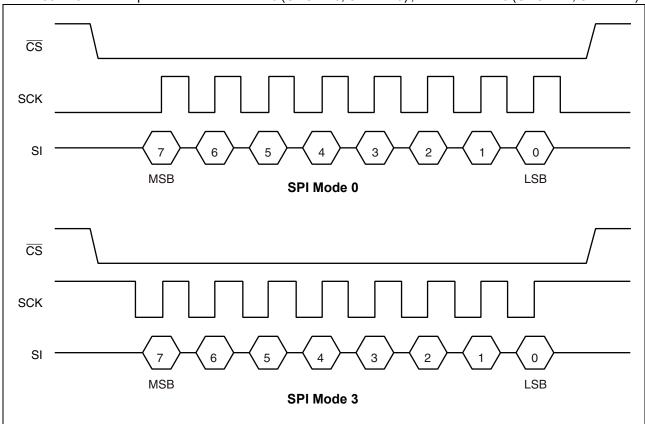
Pin No.	Pin Name	Functional description
1	CS	Chip Select pin This is an input pin to make chip select. When \overline{CS} is the "H" level, device is in deselect (standby) status and SO becomes High-Z. Inputs from other pins are ignored at this time. When \overline{CS} is the "L" level, device is in select (active) status. \overline{CS} has to be the "L" level before inputting op-code.
3	WP	Write Protect pin This is a pin to control writing to a status register. The writing of status register (see "■ STATUS REGISTER") is protected in related with WP and WPEN. See "■WRITING PROTECT" for detail.
7	HOLD	Hold pin This pin is used to interrupt serial input/output without making chip deselect. When HOLD is the "L" level, hold operation is activated, SO becomes High-Z, and SCK and SI become don't care. While the hold operation, CS shall be retained the "L" level.
6	SCK	Serial Clock pin This is a clock input pin to input/output serial data. SI is loaded synchronously to a rising edge, SO is output synchronously to a falling edge.
5	SI	Serial Data Input pin This is an input pin of serial data. This inputs op-code, address, and writing data.
2	SO	Serial Data Output pin This is an output pin of serial data. Reading data of FeRAM memory cell array and status register are output. This is High-Z during standby.
8	VDD	Supply Voltage pin
4	VSS	Ground pin
DIE PAD	—	It is allowed for the DIE PAD on the bottom of the SON8 package to be floating (no connection to anything) or to be connected to VSS.

■ BLOCK DIAGRAM



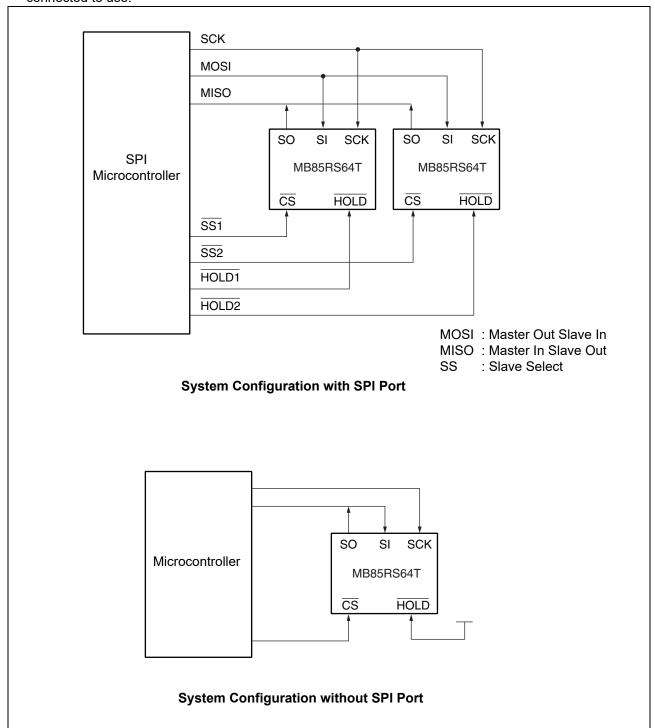
■ SPI MODE

MB85RS64T corresponds to the SPI mode 0 (CPOL = 0, CPHA = 0), and SPI mode 3 (CPOL = 1, CPHA = 1).



■ SERIAL PERIPHERAL INTERFACE (SPI)

MB85RS64T works as a slave of SPI. More than 2 devices can be connected by using microcontroller equipped with SPI port. By using a microcontroller not equipped with SPI port, SI and SO can be bus connected to use.



■ STATUS REGISTER

Bit No.	Bit Name	Function	
7	WPEN	Status Register Write Protect This is a bit composed of nonvolatile memories (FeRAM). WPEN protects writing to a status register (see "■ WRITING PROTECT") relating with WP input. Writing with the WRSR command and reading with the RDSR command are possible.	
6 to 4	_	Not Used Bits These are bits composed of nonvolatile memories, writing with the WRSR command is possible, and "000" is written before shipment. These bits are not used but they are read with the RDSR command.	
3	BP1	Block Protect This is a bit composed of nonvolatile memory. This defines size of wr	
2	BP0	protect block for the WRITE command (see "■ BLOCK PROTECT"). Writing with the WRSR command and reading with the RDSR command are possible.	
1	WEL	Write Enable Latch This indicates FeRAM Array and status register are writable. The WREN command is for setting, and the WRDI command is for resetting. With the RDSR command, reading is possible but writing is not possible with the WRSR command. WEL is reset after the following operations. After power ON. After WRDI command recognition.	
0	0	This is a bit fixed to "0".	

■ OP-CODE

MB85RS64T accepts 8 kinds of command specified in op-code. Op-code is a code composed of 8 bits shown in the table below. Do not input invalid codes other than those codes. If $\overline{\text{CS}}$ is risen while inputting op-code, the command are not performed.

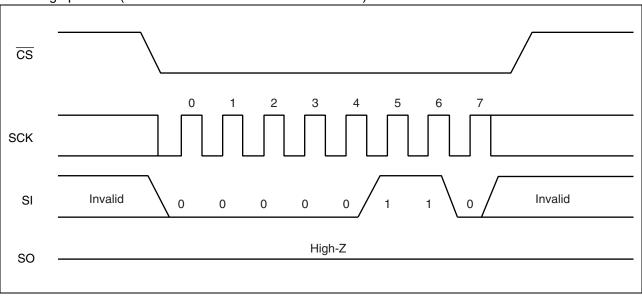
Name	Description	Op-code
WREN	Set Write Enable Latch	0000 0110в
WRDI	Reset Write Enable Latch	0000 0100в
RDSR	Read Status Register	0000 0101в
WRSR	Write Status Register	0000 0001в
READ	Read Memory Code	0000 0011в
WRITE	Write Memory Code	0000 0010в
RDID	Read Device ID	1001 1111в
SLEEP	Sleep Mode	1011 1001в
RFU	Reserved for future use*1	0000 1011в

^{*1:}When this command is input, SO output will be unvalued.

■ COMMAND

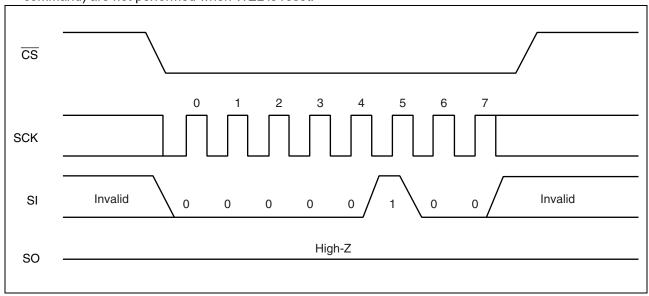
• WREN

The WREN command sets WEL (Write Enable Latch) . WEL shall be set with the WREN command before writing operation (WRSR command and WRITE command) .



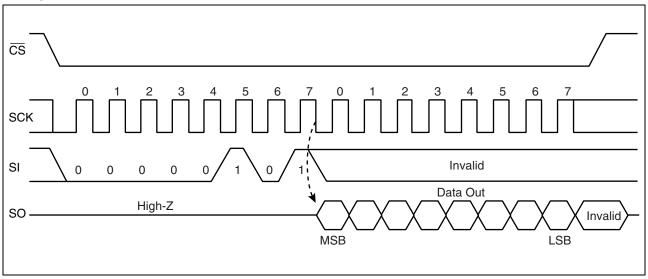
• WRDI

The WRDI command resets WEL (Write Enable Latch) . Writing operation (WRITE command and WRSR command) are not performed when WEL is reset.



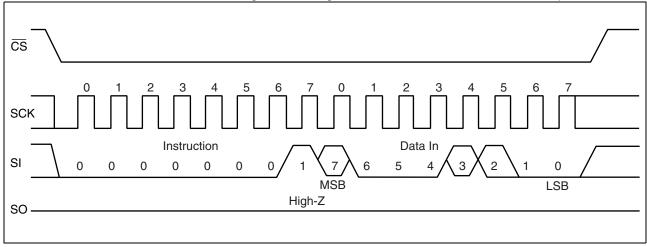
• RDSR

The RDSR command reads status register data. After op-code of RDSR is input to SI, 8-cycle clock is input to SCK. The SI value is invalid during this time. SO is output synchronously to a falling edge of SCK. In the RDSR command, repeated reading of status register is enabled by sending SCK continuously before rising of $\overline{\text{CS}}$.



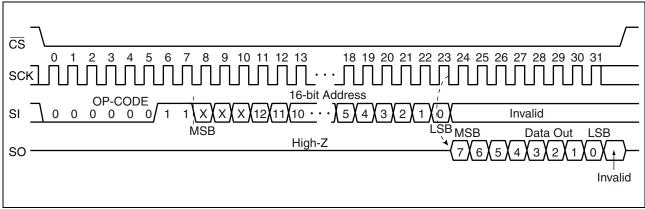
• WRSR

The WRSR command writes data to the nonvolatile memory bit of status register. After performing WRSR op-code to a SI pin, 8 bits writing data is input. WEL (Write Enable Latch) is not able to be written with WRSR command. A SI value correspondent to bit 1 is ignored. Bit 0 of the status register is fixed to "0" and cannot be written. The SI value corresponding to bit 0 is ignored. The WP signal level shall be fixed before performing the WRSR command, and do not change the WP signal level until the end of command sequence.



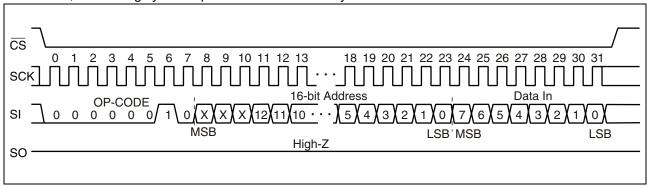
• READ

The READ command reads FeRAM memory cell array data. Arbitrary 16 bits address and op-code of READ are input to SI. The 3-bit upper address bit is invalid. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When $\overline{\text{CS}}$ is risen, the READ command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before $\overline{\text{CS}}$ rising. When it reaches the most significant address, it rolls over to the starting address, and reading cycle keeps on infinitely.



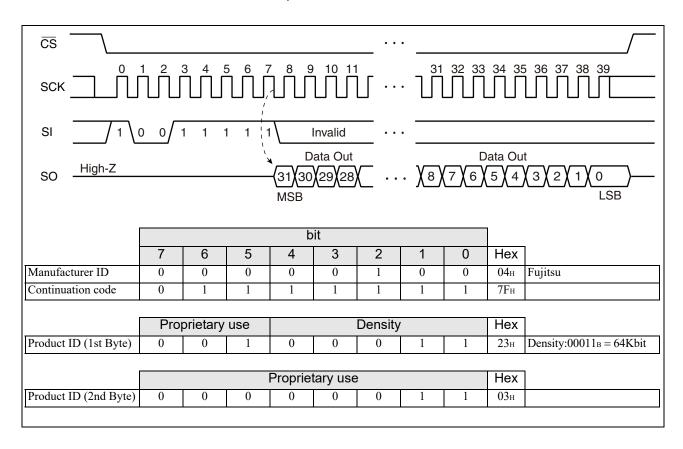
WRITE

The WRITE command writes data to FeRAM memory cell array. WRITE op-code, arbitrary 16 bits of address and 8 bits of writing data are input to SI. The 3-bit upper address bit is invalid. When 8 bits of writing data is input, data is written to FeRAM memory cell array. Risen \overline{CS} will terminate the WRITE command. However, if you continue sending the writing data for 8 bits each before \overline{CS} rising, it is possible to continue writing with automatic address increment. When it reaches the most significant address, it rolls over to the starting address, and writing cycle keeps on continued infinitely.



• RDID

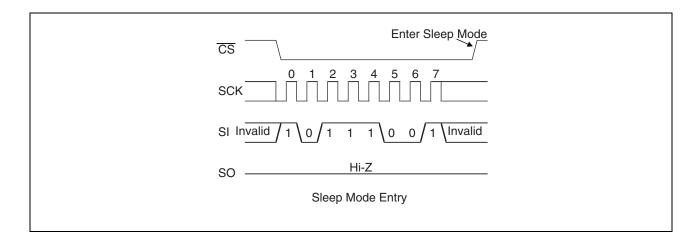
The RDID command reads fixed Device ID. After performing RDID op-code to SI, 32-cycle clock is input to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK. The output is in order of Manufacturer ID (8bit)/Continuation code (8bit)/Product ID (1st Byte)/Product ID (2nd Byte). In the RDID command, SO holds the output state of the last bit in 32-bit Device ID until \overline{CS} is risen.



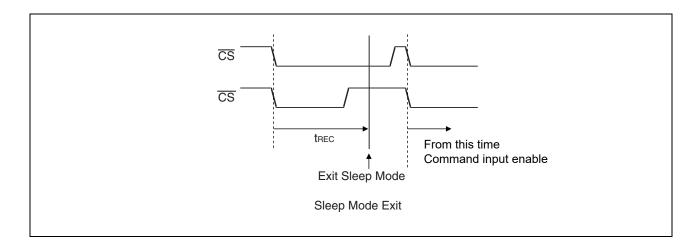
SLEEP

The SLEEP command shifts the LSI to a low power mode called "SLEEP mode". The transition to the SLEEP mode is carried out at the rising edge of \overline{CS} after operation code in the SLEEP command. However, when at least one SCK clock is inputted before the rising edge of \overline{CS} after operation code in the SLEEP command, this SLEEP command is canceled.

After the SLEEP mode transition, SCK and SI inputs are ignored and SO changes to a Hi-Z state.



Returning to an normal operation from the SLEEP mode is carried out after t_{REC} (Max 400 μs) time from the falling edge of \overline{CS} (see the figure below). It is possible to return \overline{CS} to H level before t_{REC} time. However, it is prohibited to bring down \overline{CS} to L level again during t_{REC} period.



■ BLOCK PROTECT

Writing protect block for WRITE command is configured by the value of BP0 and BP1 in the status register.

BP1	BP0	Protected Block
0	0	None
0	1	1800н to 1FFFн (upper 1/4)
1	0	1000н to 1FFFн (upper 1/2)
1	1	0000н to 1FFFн (all)

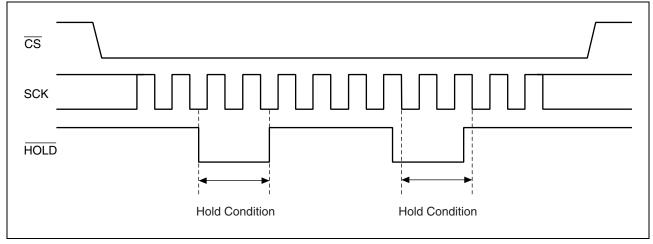
■ WRITING PROTECT

Writing operation of the WRITE command and the WRSR command are protected with the value of WEL, WPEN, WP as shown in the table.

WEL	WPEN	WP	Protected Blocks	Unprotected Blocks	Status Register
0	Х	Х	Protected	Protected	Protected
1	0	Х	Protected	Unprotected	Unprotected
1	1	0	Protected	Unprotected	Protected
1	1	1	Protected	Unprotected	Unprotected

■ HOLD OPERATION

Hold status is retained without aborting a command if HOLD is the "L" level while CS is the "L" level. The timing for starting and ending hold status depends on the SCK to be the "H" level or the "L" level when a HOLD pin input is transited to the hold condition as shown in the diagram below. In case the HOLD pin transited to "L" level when SCK is "L" level, return the HOLD pin to "H" level at SCK being "L" level. In the same manner, in case the HOLD pin transited to "L" level when SCK is "H" level, return the HOLD pin to "H" level at SCK being "H" level. Arbitrary command operation is interrupted in hold status, SCK and SI inputs become don't care. And, SO becomes High-Z while reading command (RDSR, READ). If CS is rising during hold status, a command is aborted. In case the command is aborted before its recognition, WEL holds the value before transition to hold status.



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rat	Unit	
Farailletei	Symbol	Min	Max	Oille
Power supply voltage*	V_{DD}	- 0.5	+ 4.0	V
Input voltage*	Vin	- 0.5	V _{DD} + 0.5	V
Output voltage*	Vоит	- 0.5	V _{DD} + 0.5	V
Operation ambient temperature	TA	- 40	+ 85	°C
Storage temperature	Tstg	– 55	+ 125	°C

^{*:} These parameters are based on the condition that Vss is 0 V.

WARNING: Semiconductor devices may be permanently damaged by application of stress (including, without limitation, voltage, current or temperature) in excess of absolute maximum ratings.

Do not exceed any of these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Unit		
Farameter	Symbol	Min	Тур	Max	Onit
Power supply voltage*1	V_{DD}	1.8	3.3	3.6	V
Operation ambient temperature*2	TA	- 40	_	+ 85	°C

^{*1:} These parameters are based on the condition that Vss is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated under these conditions.

Any use of semiconductor devices will be under their recommended operating condition. Operation under any conditions other than these conditions may adversely affect reliability of device and could result in device failure.

No warranty is made with respect to any use, operating conditions or combinations not represented on this data sheet. If you are considering application under any conditions other than listed herein, please contact sales representatives beforehand.

^{*2:} Ambient temperature when only this device is working. Please consider it to be the almost same as the package surface temperature.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol	Condition		Value		Unit
Faranietei	Syllibol	Condition	Min	Тур	Max	
Input leakage current*1	lu	\overline{WP} , \overline{HOLD} , SCK, \overline{CS} , $\overline{SI} = 0 \text{ V to V}_{DD}$		_	1	μА
Output leakage current*2	I LO	SO = 0 V to V _{DD}			1	μΑ
		SCK = 0.1MHz		15	_	μΑ
Operating power supply current	I _{DD}	SCK = 1 MHz		60	100	μΑ
		SCK = 10 MHz	—	500	800	μΑ
Standby current	Isa	$SCK = SI = \overline{CS} = V_{DD}$	_	9	12	μΑ
Sleep current	Izz	CS = V _{DD} all inputs V _{SS} or V _{DD}	_	4	6	μА
Input high voltage	ViH	$V_{DD} = 1.8 \text{ V to } 3.6 \text{ V}$	$V_{\text{DD}} \times 0.7$		$V_{\text{DD}} + 0.5$	V
Input low voltage	VIL	$V_{DD} = 1.8 \text{ V to } 3.6 \text{ V}$	- 0.5		$V_{\text{DD}} \times 0.3$	V
Output high voltage	Vон	Iон = −2 mA	V _{DD} - 0.5		V_{DD}	V
Output low voltage	Vol	IoL = 2 mA	Vss	_	0.4	V

^{*1:} Applicable to; $\overline{\text{CS}}$, $\overline{\text{WP}}$, $\overline{\text{HOLD}}$, SCK, SI *2: Applicable to; SO

2. AC Characteristics

Doromotor	Symbol	Va	Value		
Parameter	Symbol	Min	Max	- Unit	
SCK clock frequency	fск	0	10	MHz	
Clock high time	tсн	20	_	ns	
Clock low time	t c∟	20		ns	
Chip select set up time	t csu	10	_	ns	
Chip select hold time	tсsн	10	_	ns	
Output disable time	top		12	ns	
Output data valid time	todv		18	ns	
Output hold time	tон	0	_	ns	
Deselect time	t₀	40		ns	
Data rising time	t _R		50	ns	
Data falling time	t⊧		50	ns	
Data set up time	t su	5		ns	
Data hold time	tн	5	_	ns	
HOLD set up time	tнs	10		ns	
HOLD hold time	tнн	10		ns	
HOLD output floating time	t HZ	_	20	ns	
HOLD output active time	t ız	_	20	ns	
SLEEP resume time	trec		400	μS	

AC Test Condition

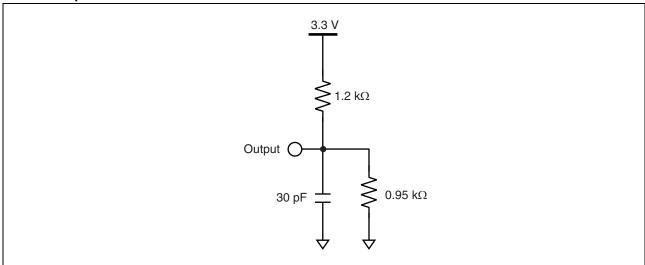
Power supply voltage : 1.8 V to 3.6 V

Operation ambient temperature : -40 °C to +85 °C

Input voltage magnitude : $0 \le V_{\text{IL}} \le 0.2 \times V_{\text{DD}}$, $0.8 \times V_{\text{DD}} \le V_{\text{IH}} \le V_{\text{DD}}$,

Input rising time: 5 ns Input falling time: 5 ns Input judge level: VDD/2 Output judge level: VDD/2

AC Load Equivalent Circuit

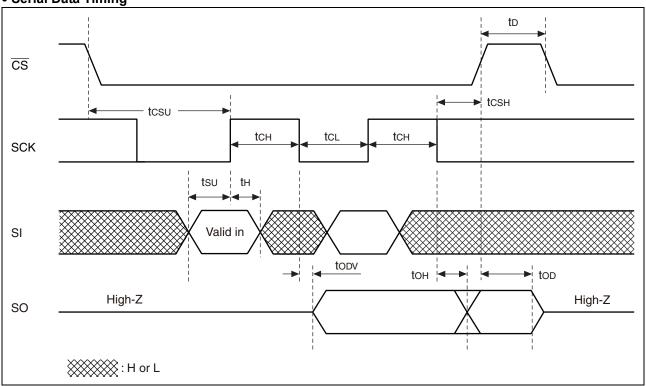


3. Pin Capacitance

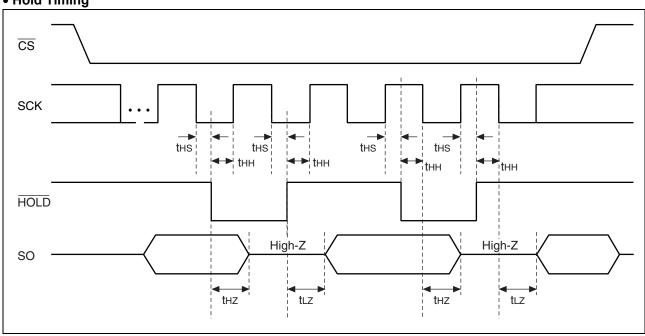
Parameter	Symbol	Conditions	Va	lue	Unit
Farameter	Symbol	Conditions	Min	Max	Oilit
Output capacitance	Со	$V_{DD} = V_{IN} = V_{OUT} = 0 V$	_	8	pF
Input capacitance	Cı	$f = 1 \text{ MHz}, T_A = +25 ^{\circ}\text{C}$	_	6	pF

■ TIMING DIAGRAM

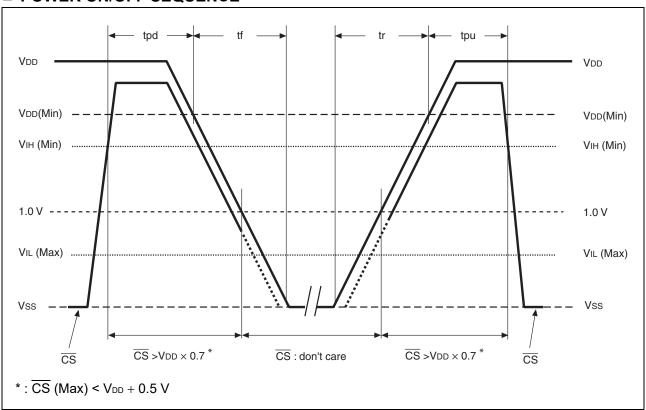
• Serial Data Timing



• Hold Timing







Parameter	Symbol	Va	Unit	
Farameter	Symbol		Max	Offic
CS level hold time at power OFF	tpd	400	_	ns
CS level hold time at power ON	tpu	250	_	μs
Power supply rising time	tr	0.05	_	ms/V
Power supply falling time	tf	0.1	_	ms/V

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

■ FeRAM CHARACTERISTICS

Item	Min	Max	Unit	Parameter
Read/Write Endurance*1	10 ¹³		Times/byte	Operation Ambient Temperature T _A = +85 °C
Data Retention*2	10		Years	Operation Ambient Temperature T _A = + 85 °C

^{*1 :} Total number of reading and writing defines the minimum value of endurance, as an FeRAM memory operates with destructive readout mechanism.

■ NOTE ON USE

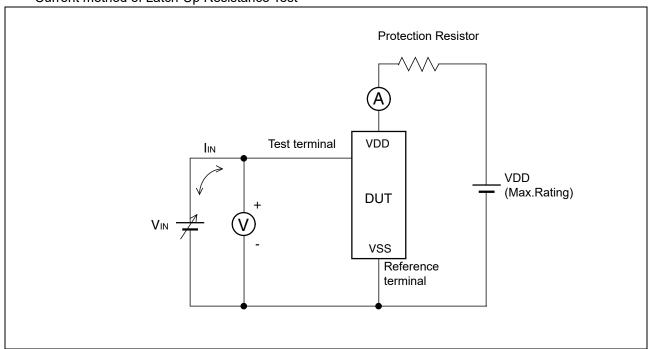
We recommend programming of the device after reflow. Data written before reflow cannot be guaranteed.

^{*2 :} Minimum values define retention time of the first reading/writing data right after shipment.

■ ESD AND LATCH-UP

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant		≥ 2000 V
ESD MM (Machine Model) JESD22-A115 compliant		≥ 200 V
ESD CDM (Charged Device Model) JESD22-C101 compliant	MB85RS64TPNF-G-JNE2 MB85RS64TPNF-G-JNERE2 MB85RS64TPN-G-AMEWE1	≥ 1000 V
Latch-Up (I-test) JESD78 compliant		_
Latch-Up (V _{supply} overvoltage test) JESD78 compliant		_
Latch-Up (Current Method) Proprietary method		_
Latch-Up (C-V Method) Proprietary method		≥ 200 V

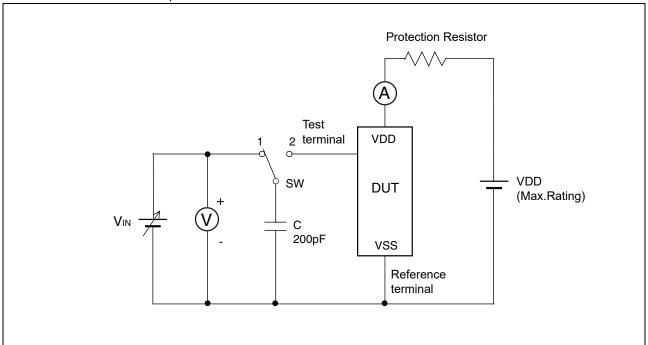
· Current method of Latch-Up Resistance Test



Note: The voltage V_{IN} is increased gradually and the current I_{IN} of 300 mA at maximum shall flow. Confirm the latch up does not occur under $I_{IN} = \pm 300$ mA.

In case the specific requirement is specified for I/O and $I_{\rm IN}$ cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement.

• C-V method of Latch-Up Resistance Test



Note: Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.

Repeat this process 5 times. However, if the latch-up condition occurs before completing 5 times, this test must be stopped immediately.

■ REFLOW CONDITIONS AND FLOOR LIFE

[JEDEC MSL] : Moisture Sensitivity Level 3 (IPC/JEDEC J-STD-020E)

■ CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES

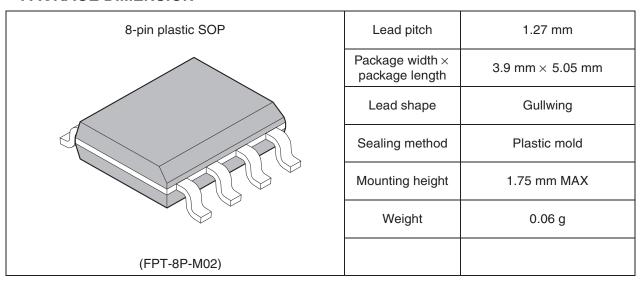
This product complies with the regulations of REACH Regulations, EU RoHS Directive and China RoHS.

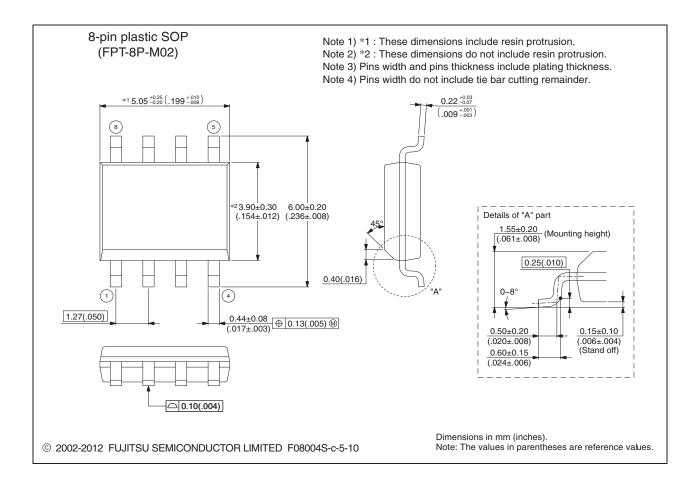
■ ORDERING INFORMATION

Part number	Package	Shipping form	Minimum shipping quantity
MB85RS64TPNF-G-JNE2 8-pin plastic SOP (FPT-8P-M02)		Tube	*
MB85RS64TPNF-G-JNERE2 8-pin plastic SOP (FPT-8P-M02)		Embossed Carrier tape	1500
MB85RS64TPN-G-AMEWE1	8-pin plastic SON (LCC-8P-M04)	Embossed Carrier tape	1500

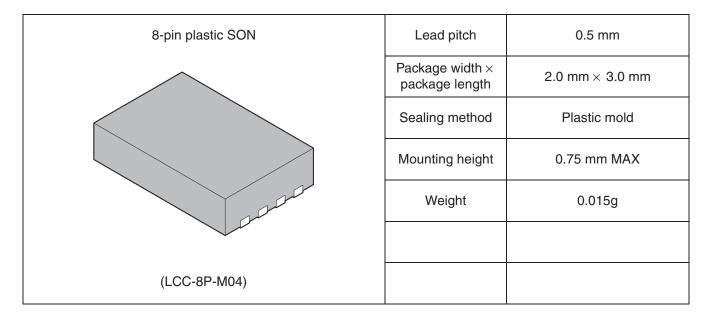
^{*:} Please contact our sales office about minimum shipping quantity.

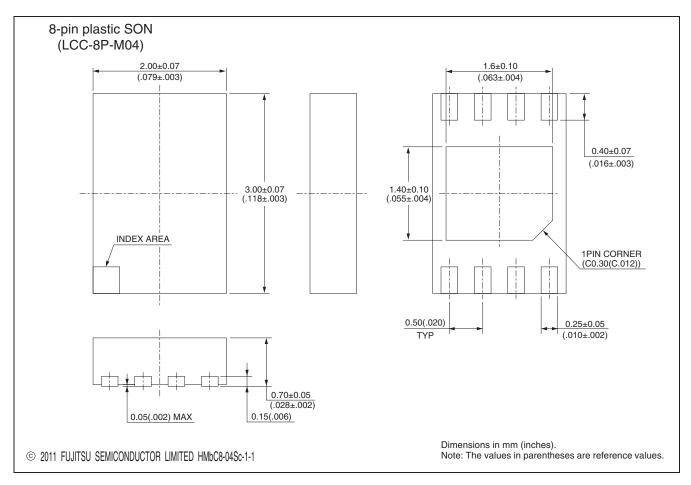
■ PACKAGE DIMENSION





(continued)





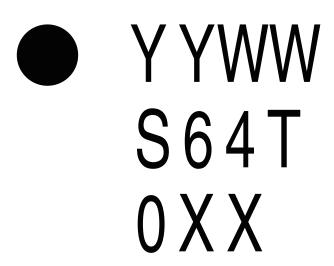
■ MARKING

[MB85RS64TPNF-G-JNE2] [MB85RS64TPNF-G-JNERE2]

RS64T E2YYWW 3XX

[FPT-8P-M02]

[MB85RS64TPN-G-AMEWE1]



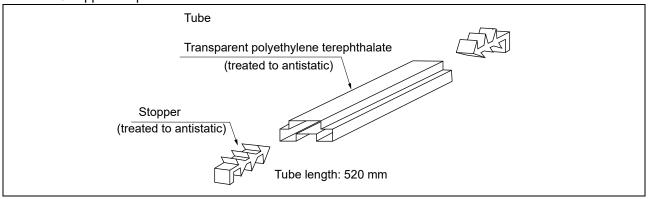
[LCC-8P-M04]

■ PACKING INFORMATION

1. Tube

1.1 Tube Dimensions

• Tube/stopper shape

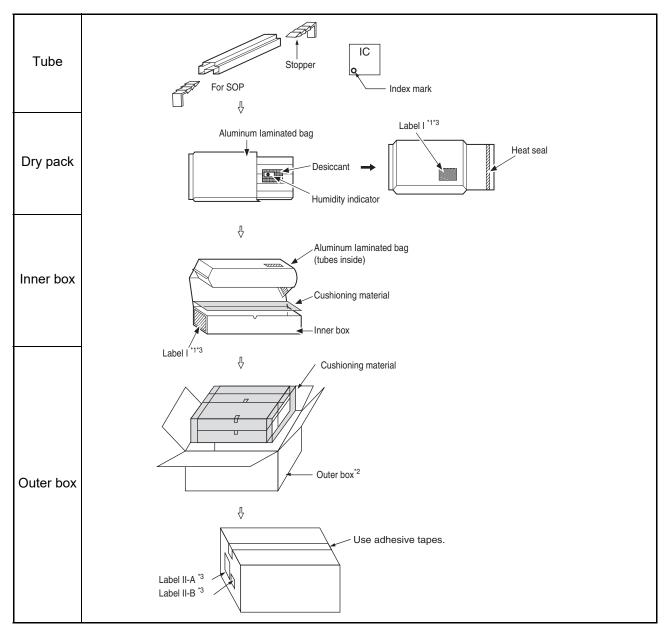


Tube cross-sections and Maximum quantity

		Maximum quantity			
Package form	Package code	pcs/ tube	pcs/inner box	pcs/outer box	
SOP, 8, plastic (2)	FPT-8P-M02	95	7600	30400	
7.4 6.4 7.4 6.4 7.4 8.4 8.4 8.4 8.4 8.4					
©2006-2010 FUJITSU SEMICONDUCTOR LIMITED F08008-SET1-PET:FJ99L-0022-E0008-1-K-3					
t = 0.5 Transparent polyethylene terephthalate					

(Dimensions in mm)

1.2 Tube Dry pack packing specifications



^{*1:} For a product of witch part number is suffixed with "E1" or "E2", a " [G] (N)" marks is display to the moisture barrier bag and the inner boxes.

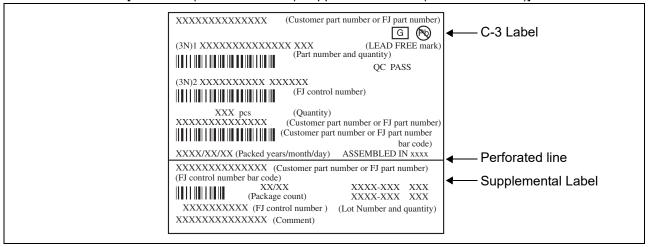
Note: The packing specifications may not be applied when the product is delivered via a distributor.

^{*2:} The space in the outer box will be filled with empty inner boxes, or cushions, etc.

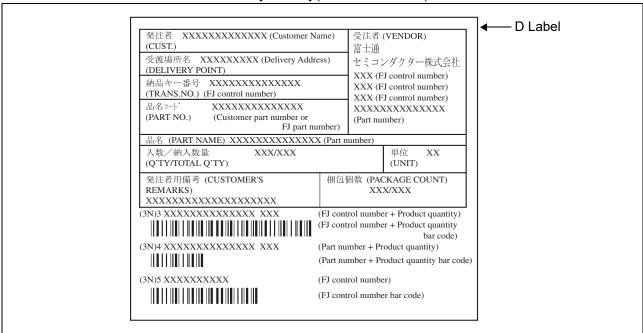
^{*3:} Please refer to an attached sheet about the indication label.

1.3 Product label indicators

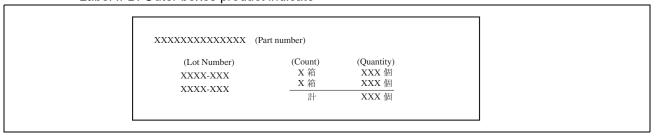
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



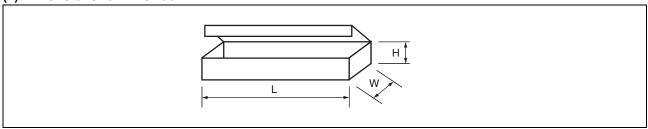
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

1.4 Dimensions for Containers

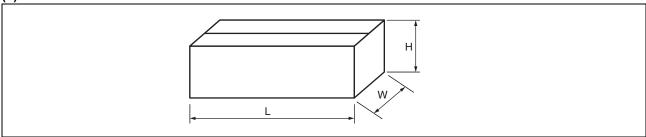
(1) Dimensions for inner box



L	W	Н
540	125	75

(Dimensions in mm)

(2) Dimensions for outer box



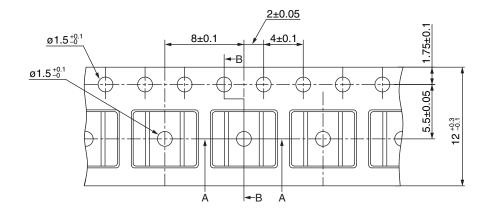
L	W	Н
565	270	180

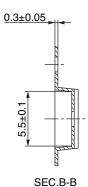
(Dimensions in mm)

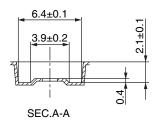
2. Emboss Tape

2.1 Tape Dimensions

PKG code	Reel No	Maximum storage capacity			
	11001110	pcs/reel	pcs/inner box	pcs/outer box	
FPT-8P-M02	3	1500	1500	10500	







© 2012 FUJITSU SEMICONDUCTOR LIMITED SOL8-EMBOSSTAPE9: NFME-EMB-X0084-1-P-1

(Dimensions in mm)

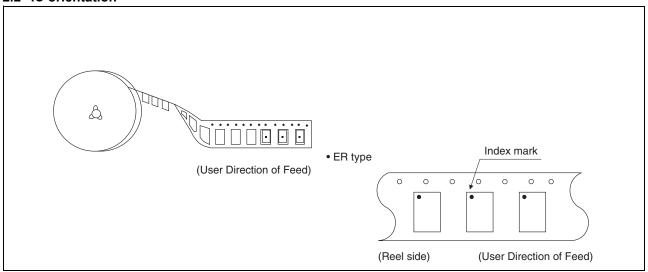
Material: Conductive polystyrene

Heat proof temperature : No heat resistance.

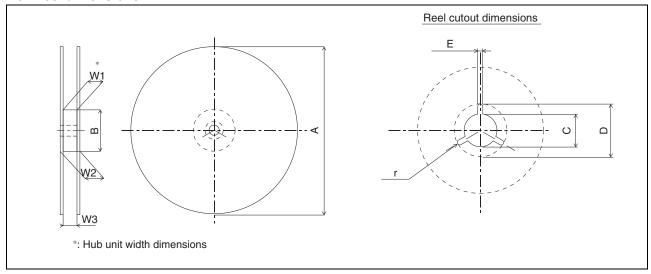
Package should not be baked

by using tape and reel.

2.2 IC orientation

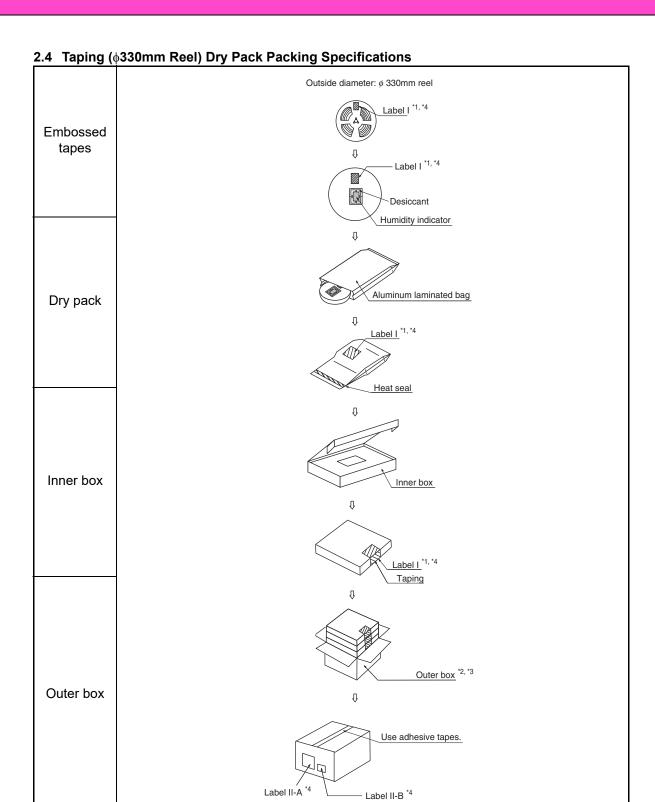


2.3 Reel dimensions



Dimensions in mm

														IIIICIIOIOI	
Reel No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
Tape width Symbol	8	1	2	1	6	2	4	3:	2	4	4	56	12	16	24
Α	254 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2				330) ± 2			
В		$100^{+2}_{-0} \qquad 100^{+2}_{-0} 150^{+2}_{-0} 100^{+2}_{-0} 150^{+2}_{-0} 100^{+2}_{-0} 100^{+2}_{-0} 100^{+2}_{-0}$													
С		13 ± 0.2 13 ^{+0.5} _{-0.2}													
D		21 ± 0.8 20.5 ⁺¹ _{-0.2}													
E		2 ± 0.5													
W1	8.4 -0	$8.4_{-0}^{+2} \qquad 12.4_{-0}^{+2} \qquad 16.4_{-0}^{+2} \qquad 24.4_{-0}^{+2} \qquad 32.4_{-0}^{+2} \qquad 44.4_{-0}^{+2} \qquad 56.4_{-0}^{+2} \qquad 16.4_{-0}^{+2} \qquad 16.4_$						12.4 +1	16.4 +1	24.4+0.1					
W2	less than 18.4 less than 18.4 less than 22.4 less than 30.4 less than 38.4 less than 50.4 less than 62.4						less than 18.4	less than 22.4	less than 30.4						
W3	7.9 ~ 10.9	11.9 ~	~ 15.4	15.9	15.9 ~ 19.4 23.9 ~ 27.4 31.9 ~ 35.4 43.9 ~ 47.4 55.9 ~ 59.4				12.4 ~ 14.4	16.4 ~ 18.4	24.4 ~ 26.4				
r		1.0													

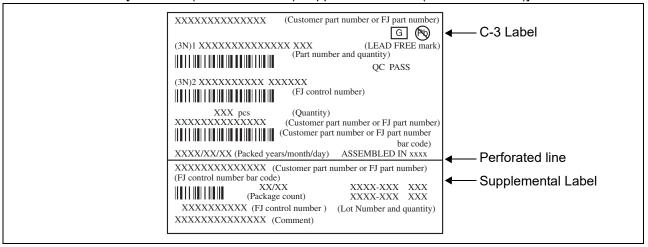


- *1: For a product of witch part number is suffixed with "E1" or "E2", a " G ® " marks is display to the moisture barrier bag and the inner boxes.
- *2: The size of the outer box may be changed depending on the quantity of inner boxes.
- *3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.
- *4: Please refer to an attached sheet about the indication label.

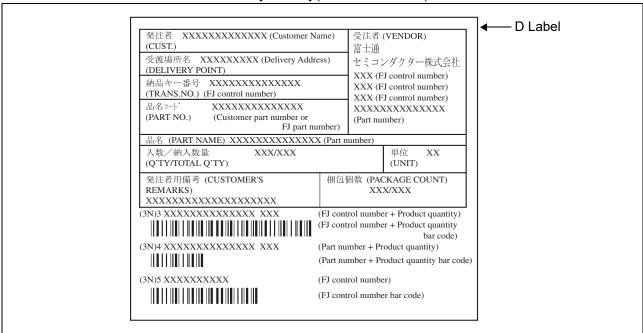
Note: The packing specifications may not be applied when the product is delivered via a distributor.

2.5 Product label indicators

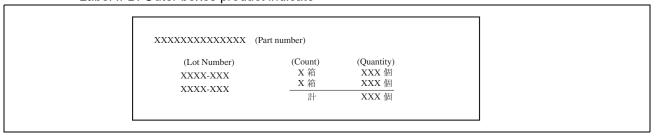
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



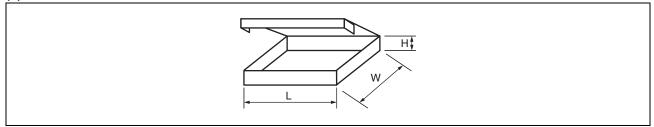
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

2.6 Dimensions for Containers

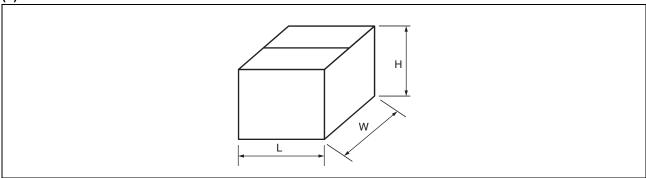
(1) Dimensions for inner box



Tape width	L	W	Н
12, 16	365		40
24, 32		345	50
44		343	65
56			75

(Dimensions in mm)

(2) Dimensions for outer box



L	W	Н
415	400	315

(Dimensions in mm)

■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

Page	Section	Change Results
_	Overall	Following word is revised to more commonly used one. FRAM to FeRAM

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